FORMING METHOD FOR RESISTANCE ELEMENT OF SEMICONDUCTOR DEVICE

Patent number: JP4014863
Publication date: 1992-01-20
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Classification:
- international: H01L27/04
- european:
Application number: JP19900117928 19900508
Priority number(s): JP19900117928 19900508

Abstract of **JP4014863**

PURPOSE:To obtain a resistance element having high resistance without increasing the length of the element by forming a second conductivity type region partly at the element, and reducing the sectional area of the resistance part to be conducted.
CONSTITUTION:Part of a high resistor 3A except a region S2 is masked with photoresist, and P-type impurity ions such as second conductivity type boron, etc., are so implanted in polycrystalline silicon 3 of the region S2 in a predetermined depth. Thus, the region S2 becomes a reverse conductivity type region 4 of second conductivity type to form a junction to a region S1 in which an N-type impurities are implanted. Thereafter, with photoresist as a mask an unnecessary part is etched to form a resistance element R of the resistor 3A and the region 4, and a wiring W is formed of a low resistor 3B. Thus, even if a current is fed in an arbitrary direction in the region 4, a current is scarcely fed, and the resistor 3A formed previously is reduced in sectional area in thickness corresponding to the region 4, thereby enhancing its resistance value.